查询TPC8102供应商

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (π−MOSVI)

TPC8102

Lithium Ion Battery Applications

Notebook PCs

Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain−source ON resistance : $R_{DS\ (ON)}$ = 34 mΩ (typ.)
- High forward transfer admittance : $|Y_{fs}|$ = 9 S (typ.)
- Low leakage current : I_{DSS} = −10 μA (max) (V_{DS} = −30 V)
- Enhancement−mode : V_{th} = −0.8~ −2.0 V (V_{DS} = −10 V, ID = −1 mA)

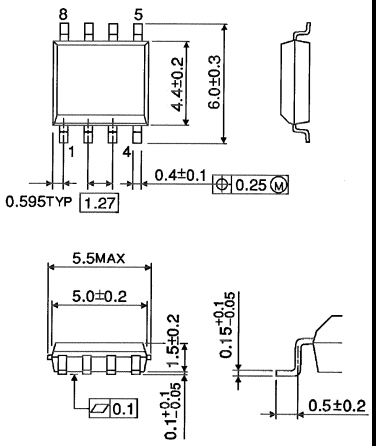
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	−30	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	−6	A
	Pulse (Note 1)	I_{DP}	−24	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	2.4	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.0	W
Single pulse avalanche energy (Note 3)		E_{AS}	47	mJ
Avalanche current		I_{AR}	−6	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	0.24	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: For (Note 1), (Note 2), (Note 3) and (Note 4), please refer to the next page.

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

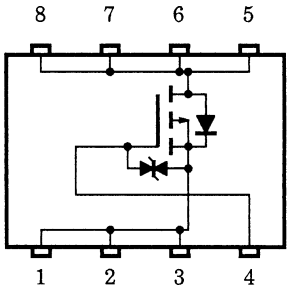


1, 2, 3 SOURCE
4 GATE
5, 6, 7, 8 DRAIN

JEDEC	—
JEITA	—
TOSHIBA	2-6J1B

Weight: 0.080 g (typ.)

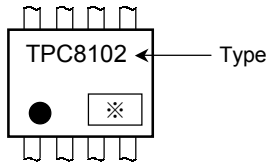
Circuit Configuration



Thermal Characteristics

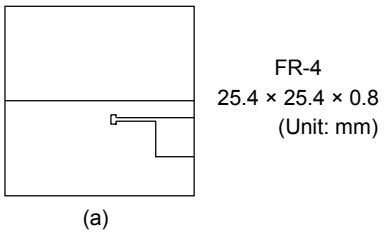
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	52.1	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	125	°C/W

Marking (Note 5)

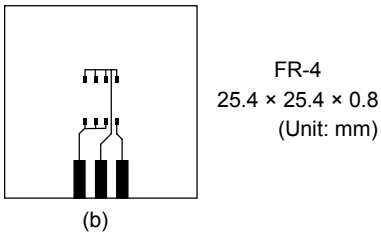


Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)



(b)

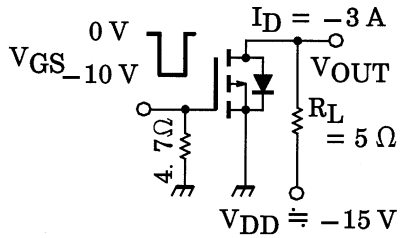
Note 3: V_{DD} = −24 V, T_{ch} = 25°C (initial), L = 1.0 mH, R_G = 25 Ω, I_{AR} = −6 A

Note 4: Reptitve rating; pulse width limited by maximum channel temperature.

Note 5: ● on lower left of the marking indicates Pin 1.

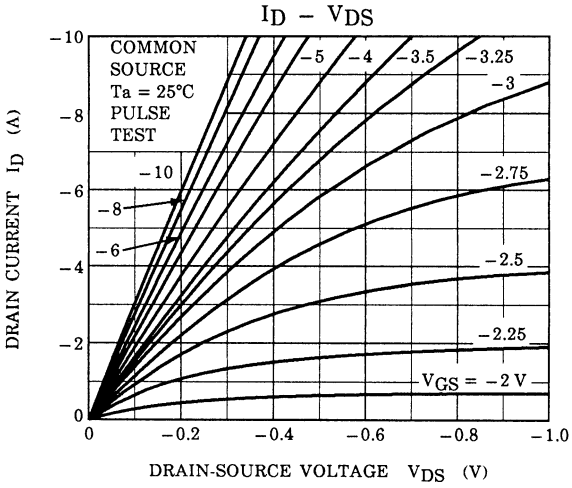
※ shows Lot number. (year of manufacture: last decimal digit of the year of manufacture, month of manufacture: january to december are denoted by letters A to L respectively)

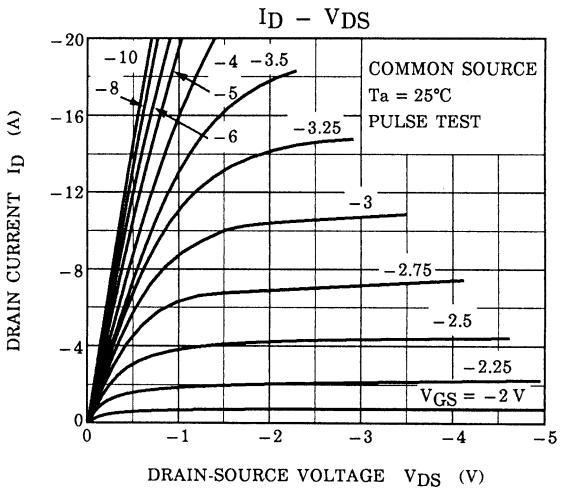
Electrical Characteristics (Ta = 25°C)

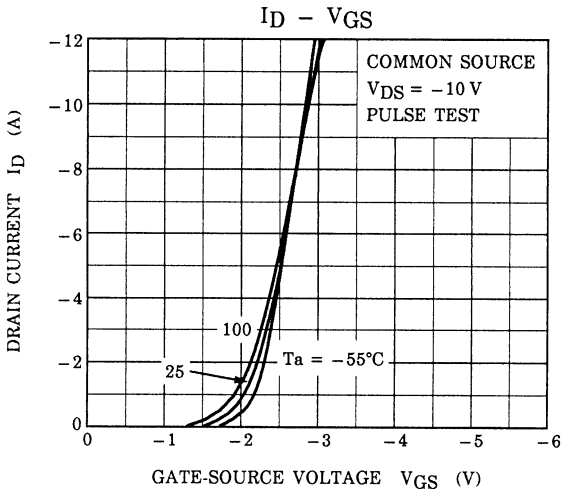
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut−off current		I_{DSS}	V_{DS} = −30 V, V_{GS} = 0 V	—	—	−10	μA
Drain −source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−30	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = −1 mA	−0.8	—	−2.0	V
Drain−source ON resistance		$R_{DS\ (ON)}$	V_{GS} = −4 V, I_D = −3 A	—	56	70	mΩ
		$R_{DS\ (ON)}$	V_{GS} = −10 V, I_D = −3 A	—	34	40	mΩ
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −3 A	4.5	9	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	1380	—	pF
Reverse transfer capacitance		C_{rss}		—	220	—	
Output capacitance		C_{oss}		—	560	—	
Switching time	Rise time	t_r		—	12	—	ns
	Turn−on time	t_{on}		—	20	—	
	Fall time	t_f		—	22	—	
	Turn−off time	t_{off}		—	90	—	
Total gate charge (Gate−source plus gate−drain)		Q_g	V_{DD} ≈ −24 V, V_{GS} = −10 V, I_D = −6 A	—	43	—	nC
Gate−source charge		Q_{gs}		—	30	—	
Gate−drain (“miller”) charge		Q_{gd}		—	13	—	

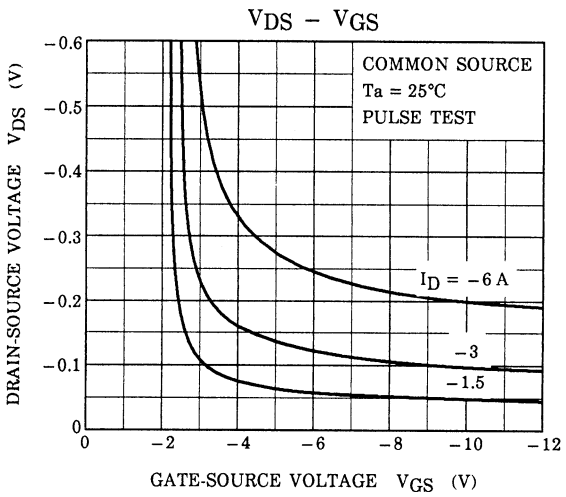
Source−Drain Ratings and Characteristics (Ta = 25°C)

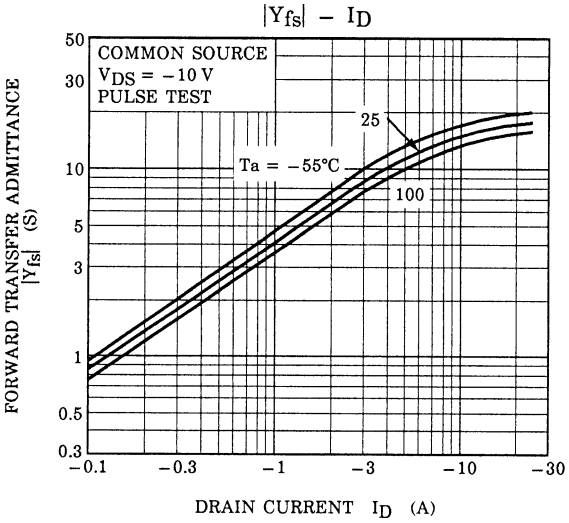
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	−24	A
Forward voltage (diode)		V_{DSF}	I_{DR} = −6 A, V_{GS} = 0 V	—	—	1.2	V

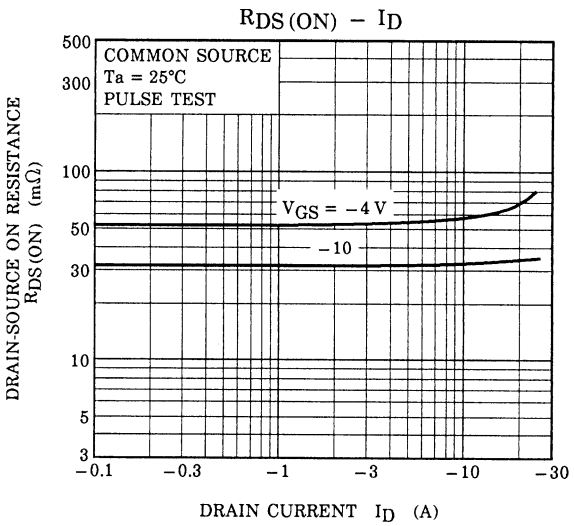

I_D – V_{DS}
COMMON SOURCE
Ta = 25°C
PULSE TEST
−10
−8
−6
−5
−4
−3.5
−3.25
−3
−2.75
−2.5
−2.25
V_{GS} = −2 V
DRAIN CURRENT I_D (A)
DRAIN-SOURCE VOLTAGE V_{DS} (V)


I_D – V_{DS}
COMMON SOURCE
Ta = 25°C
PULSE TEST
−10
−8
−6
−5
−4
−3.5
−3.25
−3
−2.75
−2.5
−2.25
V_{GS} = −2 V
DRAIN CURRENT I_D (A)
DRAIN-SOURCE VOLTAGE V_{DS} (V)

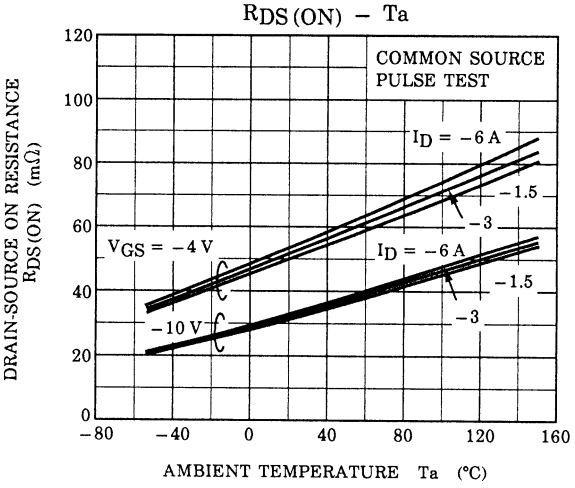

I_D – V_{GS}
COMMON SOURCE
V_{DS} = −10 V
PULSE TEST
100
25
Ta = −55°C
DRAIN CURRENT I_D (A)
GATE-SOURCE VOLTAGE V_{GS} (V)


V_{DS} – V_{GS}
COMMON SOURCE
Ta = 25°C
PULSE TEST
I_D = −6 A
−3
−1.5
DRAIN-SOURCE VOLTAGE V_{DS} (V)
GATE-SOURCE VOLTAGE V_{GS} (V)

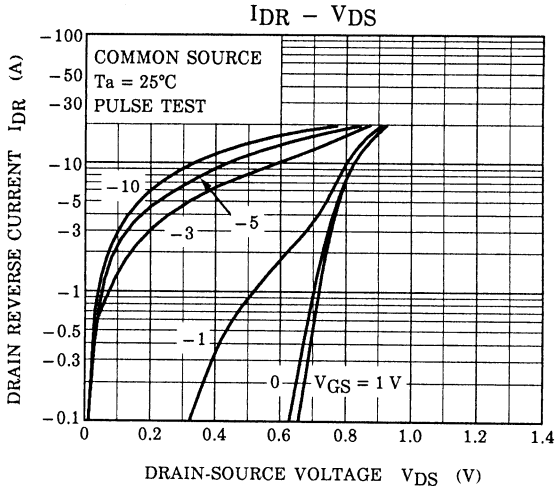

$|Y_{fs}|$ – I_D
COMMON SOURCE
V_{DS} = −10 V
PULSE TEST
25
Ta = −55°C
100
FORWARD TRANSFER ADMITTANCE $|Y_{fs}|$ (S)
DRAIN CURRENT I_D (A)


$R_{DS\,(ON)}$ – I_D
COMMON SOURCE
Ta = 25°C
PULSE TEST
V_{GS} = −4 V
−10
DRAIN-SOURCE ON RESISTANCE $R_{DS\,(ON)}$ (mΩ)
DRAIN CURRENT I_D (A)

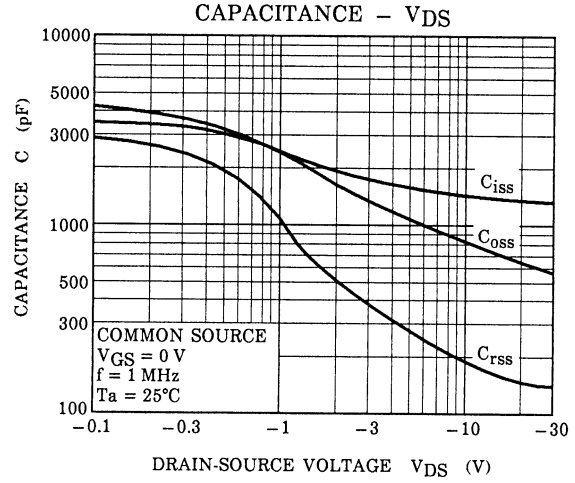
$R_{DS\,(ON)}$ – Ta



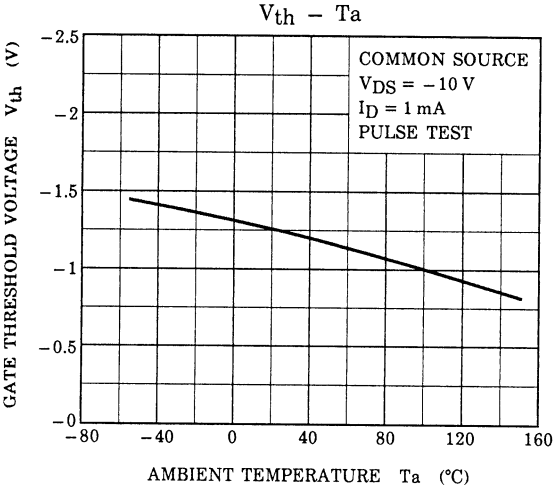
I_{DR} – V_{DS}



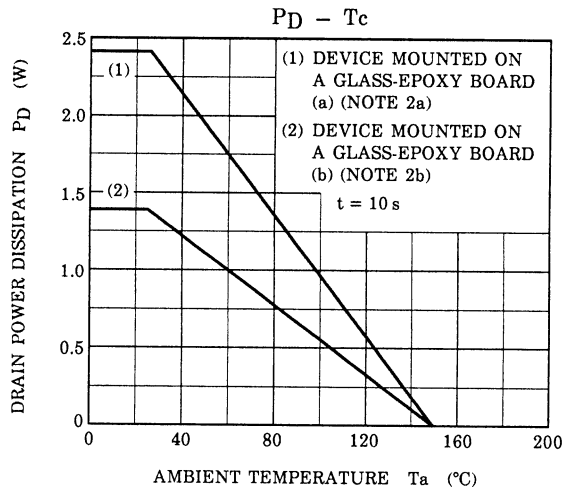
CAPACITANCE – V_{DS}



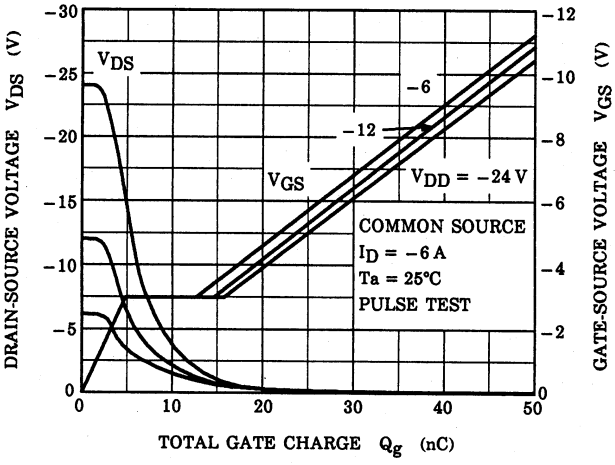
V_{th} – Ta



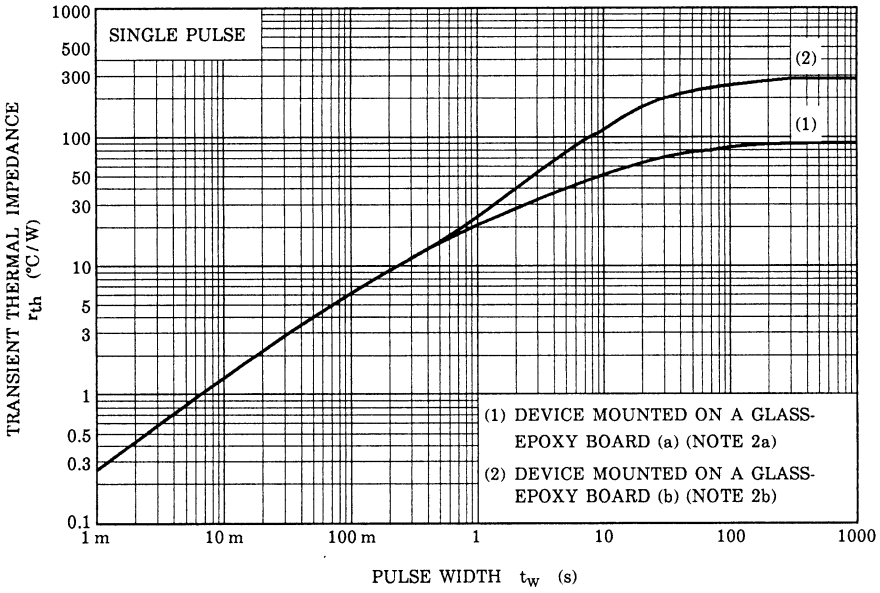
P_D – Tc


(1) DEVICE MOUNTED ON A GLASS-EPOXY BOARD (a) (NOTE 2a)
(2) DEVICE MOUNTED ON A GLASS-EPOXY BOARD (b) (NOTE 2b)
t = 10 s
(1)
(2)
DRAIN POWER DISSIPATION P_D (W)
AMBIENT TEMPERATURE Ta (°C)

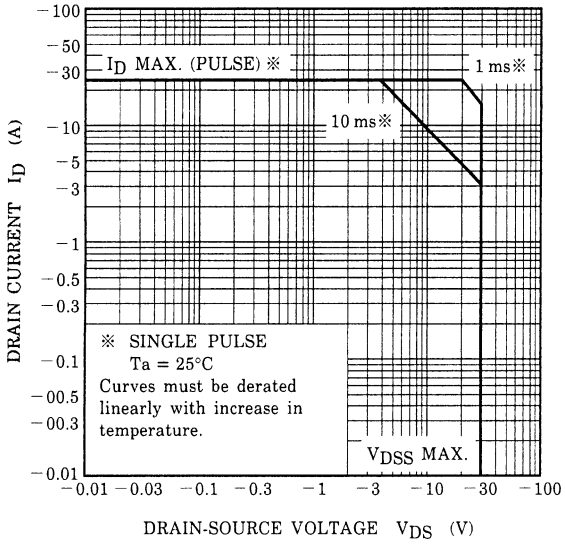
DYNAMIC INPUT / OUTPUT CHARACTERISTICS



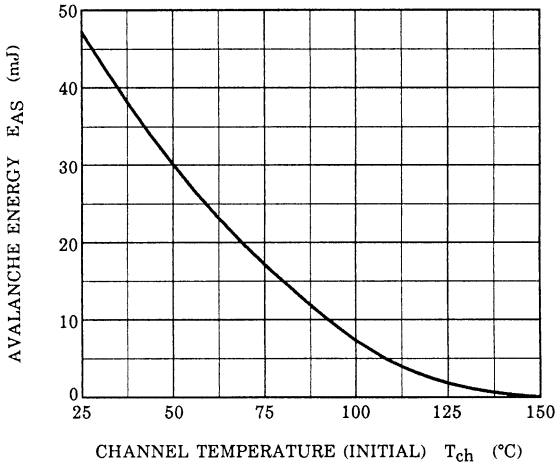
r_{th} – t_w

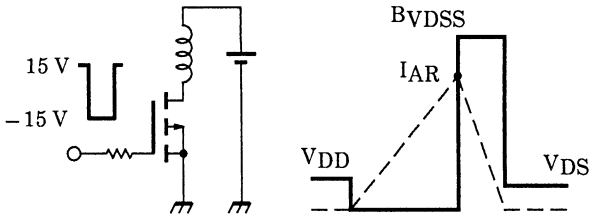


SAFE OPERATING AREA



E_{AS} – T_{ch}





TEST CIRCUIT WAVE FORM

T_{ch} = 25°C (Initial)
Peak I_{AR} = −6 A, R_G = 25 Ω
V_{DD} = −24 V, L = 1.0 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}}\right)$$

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000707EAA

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